

DESCRIPTION

Mitsubishi 2SK492 is a super mini outline resin sealed silicon N channel junction type FET. It is designed for low frequency voltage amplify,application and analog switch application.

FEATURE

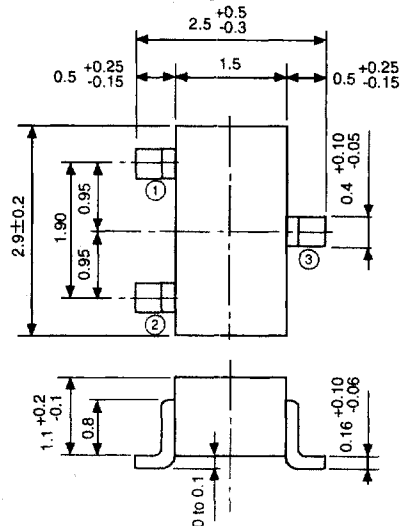
- Small type for mounting
- High $|y_{fs}|$ $|y_{fs}|=8\text{mS}(\text{typ})$
- Low $R_{DS(ON)}$ $R_{DS(ON)}=70\Omega$ typ

APPLICATION

General purpose voltage amplify,analog switch circuit
for stereo,cassette deck,VCR.

OUTLINE DRAWING

Unit:mm



TERMINAL CONNECTOR

- ① : SOURCE
- ② : DRAIN
- ③ : GATE

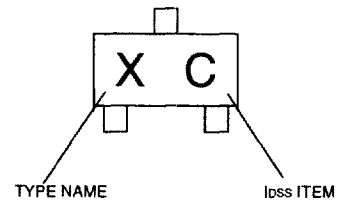
EIAJ : SC-59

JEDEC : TO-236 resemblance

Note)

The dimension without tolerance represent central value.

MARKING



MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Ratings	Unit
V_{GS}	Gate to Drain voltage	-50	V
I_G	Gate current	10	mA
P_T	Total allowable dissipation(Ta=25°C)	150	mW
T_{ch}	Channel temperature	+125	°C
T_{stg}	Storage temperature	-55 to +125	°C

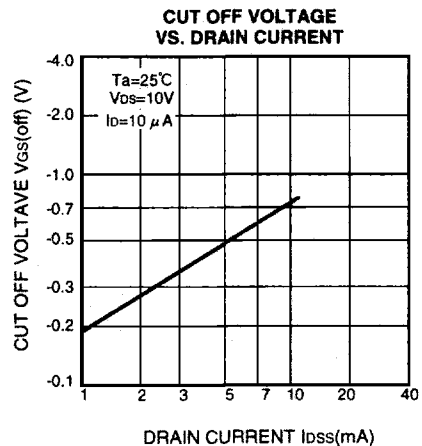
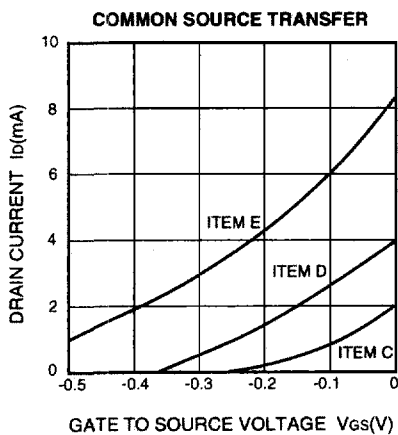
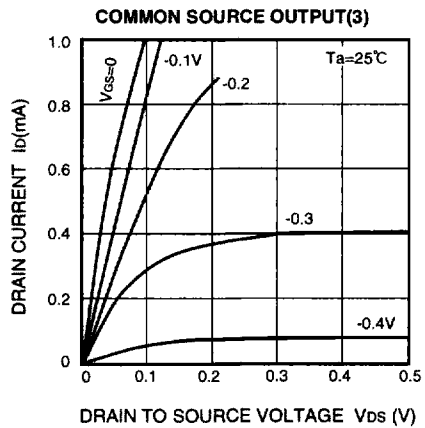
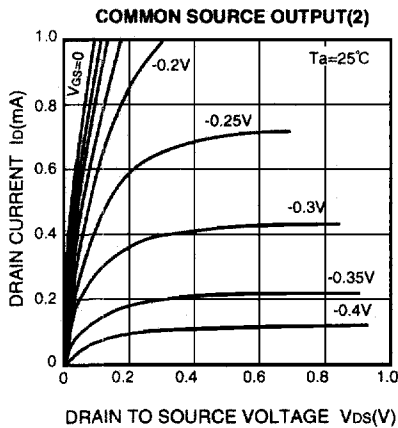
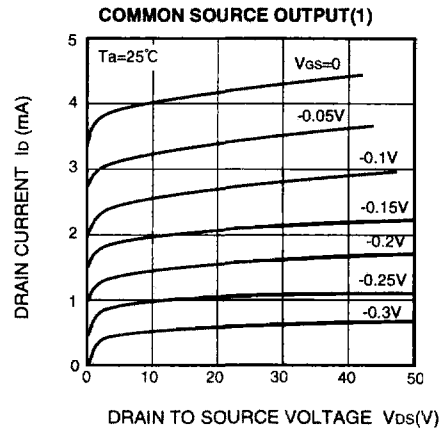
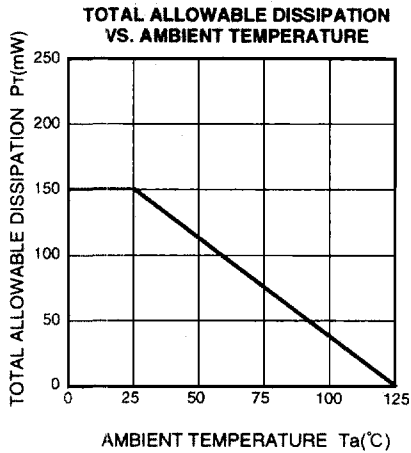
ELECTRICAL CHARACTERISTICS (Ta=25°C)

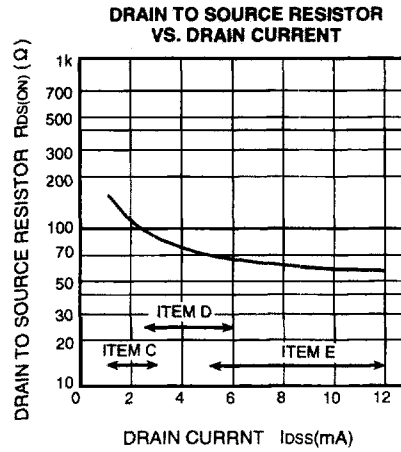
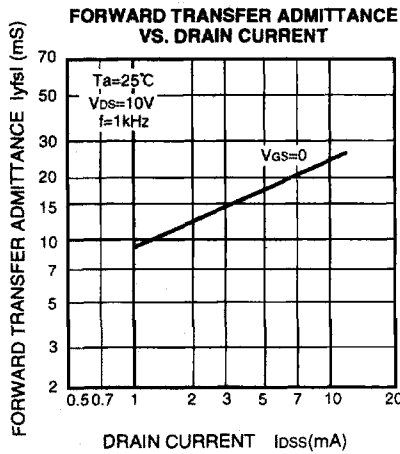
Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
I_{GSS}	Gate leakage current	$V_{GS}=-30V, V_{DS}=0$			-1	nA
I_{DSS}^*	Drain current	$V_{DS}=10V, V_{GS}=0$	1	4	12	mA
$V_{GS(off)}$	Cut off voltage	$V_{DS}=10V, I_D=10\mu A$	-0.1		-2.0	V
$ y_{fs} $	Forward transfer admittance	$V_{DS}=10V, V_{GS}=0, f=1kHz$	6.0	15		mS
$ y_{fs} $	Forward transfer admittance	$V_{DS}=10V, I_D=1mA, f=1kHz$		8		mS
$ y_{os} $	Output admittance	$V_{DS}=10V, I_D=1mA, f=1kHz$		10		μS
C_{iss}	Input capacitance	$V_{DS}=10V, V_{GS}=0, f=1MHz$		20		pF
NF	Noise figure	$V_{DS}=10V, I_D=1mA, f=100Hz, R_G=1k\Omega$		1.0		dB
$R_{DS(ON)}$	Drain to source resistor	$V_{DS}=10mVrms(1kHz), V_{GS}=0, I_{DSS}=5mA$		70		Ω

* : It shows loss classification in right table.

Item	C	D	E
I_{DSS}	1.0 to 3.0	2.5 to 6.0	5.0 to 12

TYPICAL CHARACTERISTICS





DRAIN TO SOURCE RESISTOR $R_{DS(ON)}$ TEST CIRCUIT

